

L Number	Hits	Search Text	DB	Time stamp
1	1	6159643.pn.	USPAT	2004/08/12 11:03
2	45	Goldstein-Michael.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:04
-	15760	((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)	USPAT	2004/07/27 12:18
-	1823	((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3))	USPAT	2004/06/28 10:48
-	97	(((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and ((thermal adj expansion) or (titanium adj silicate)))	USPAT	2004/06/28 12:12
-	285	(((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and isotropic\$3	USPAT	2004/06/28 12:13
-	272	(((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and isotropic\$3 not (((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and ((thermal adj expansion) or (titanium adj silicate))))	USPAT	2004/06/28 12:13
-	243	(((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and isotropic\$3 not (((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and ((thermal adj expansion) or (titanium adj silicate)))) and @ay<=2001	USPAT	2004/06/28 12:46
-	226	(((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and isotropic\$3 not (((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon) and (polish or polishing or cmp or planarize or planarization)) and (thermal adj anneal\$3)) and ((thermal adj expansion) or (titanium adj silicate)))) and @ay<=2001) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)	USPAT	2004/06/28 12:47

-	28163	((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)	USPAT	2004/07/27 12:18
-	1499	((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)) and (sacrificial with (oxide or dioxide or SiO or SiO?sub.2)))	USPAT	2004/07/27 12:24
-	264	((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)) and (sacrificial with (oxide or dioxide or SiO or SiO?sub.2) same (isotropic\$3 or (wet adj etch\$3))))	USPAT	2004/07/27 13:46
-	264	((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)) and (((sacrificial with (oxide or dioxide or SiO or SiO?sub.2) same (isotropic\$3 or (wet adj etch\$3))))	USPAT	2004/07/27 12:26
-	232	(((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)) and (((sacrificial with (oxide or dioxide or SiO or SiO?sub.2) same (isotropic\$3 or (wet adj etch\$3)))) and @ay<=2001	USPAT	2004/07/27 12:26
-	185	(((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)) and (((sacrificial with (oxide or dioxide or SiO or SiO?sub.2) same (isotropic\$3 or (wet adj etch\$3)))) and @ay<=2001) and (photo\$1lithograph\$3 or lithograph\$3)	USPAT	2004/07/27 12:27
-	169	(((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)) and (((sacrificial with (oxide or dioxide or SiO or SiO?sub.2) same (isotropic\$3 or (wet adj etch\$3)))) and @ay<=2001) and (photo\$1lithograph\$3 or lithograph\$3)) and semiconductor	USPAT	2004/07/27 13:24
-	7	("5171699" "5194394" "5340756" "5387528" "5404040" "5656520" "5668026").PN.	USPAT	2004/07/27 13:21
-	4259	(CTE or (coefficient adj3 thermal adj expansion)) and (polish or polished or polishing or cmp or planarize or planarizing)	USPAT	2004/07/27 13:46

-	4253	((CTE or (coefficient adj3 thermal adj expansion)) and (polish or polished or polishing or cmp or planarize or planarizing)) not ((((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)) and (((sacrificial with (oxide or dioxide or SiO or SiO?sub.2)) same (isotropic\$3 or (wet adj etch\$3)))) and @ay<=2001) and (photo\$1lithograph\$3 or lithograph\$3)) and semiconductor)	USPAT	2004/07/27 13:46
-	1499	((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)) and (sacrificial with (oxide or dioxide or SiO or SiO?sub.2))	USPAT	2004/07/27 13:48
-	77	((CTE or (coefficient adj3 thermal adj expansion)) and (polish or polished or polishing or cmp or planarize or planarizing)) not ((((((crystall\$3 near3 silicon) or (poly\$1crystalline adj silicon) or polysilicon or TiSi or (titanium adj silicate) or ceramic) and (polish or polishing or cmp or planarize or planarization)) and (((sacrificial with (oxide or dioxide or SiO or SiO?sub.2)) same (isotropic\$3 or (wet adj etch\$3)))) and @ay<=2001) and (photo\$1lithograph\$3 or lithograph\$3)) and semiconductor)) and (sacrificial with (oxide or dioxide or SiO or SiO?sub.2))	USPAT	2004/07/27 14:28
-	26	(mirror with photo\$1lithograph\$3).clm.	USPAT	2004/07/27 15:30
-	425	mirror with photo\$1lithograph\$3	USPAT	2004/07/27 15:30
-	3060	(mirror or glass) with photo\$1lithograph\$3	USPAT	2004/07/27 15:30
-	507	((mirror or glass) with photo\$1lithograph\$3) and (polish or polishing or cmp or planarization or planarize or planarizing)	USPAT	2004/07/27 15:31
-	326	((mirror or glass) with photo\$1lithograph\$3) and (polish or polishing or cmp or planarization or planarize or planarizing)) and (sacrificial or (silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)	USPAT	2004/07/27 15:32
-	307	((mirror or glass) with photo\$1lithograph\$3) and (polish or polishing or cmp or planarization or planarize or planarizing)) and (sacrificial or (silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)) and @ay<=2001	USPAT	2004/07/27 15:33
-	213	((mirror or glass) with photo\$1lithograph\$3) and (polish or polishing or cmp or planarization or planarize or planarizing)) and (sacrificial or (silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)) and @ay<=2001) and (crystal or crytalline or poly\$1silicon or poly\$1crystalline)	USPAT	2004/07/27 15:37

-	174	((((mirror or glass) with photo\$1lithograph\$3) and (polish or polishing or cmp or planarization or planarize or planarizing)) and (sacrificial or (silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)) and @ay<=2001) and (crystal or crytalline or poly\$1silicon or poly\$1crystalline)) and semiconductor	USPAT	2004/07/27 15:37
-	5187	((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor	USPAT	2004/08/10 16:46
-	4348	((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor	USPAT	2004/08/10 10:43
-	1443	((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)	USPAT	2004/08/10 15:54
-	314	((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)) and ((silicon adj dioxide) or (silicon adj oxide) or SiO or SiO?sub.2) with (thermal or grow or growing))	USPAT	2004/08/10 10:45
-	289	((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)) and ((silicon adj dioxide) or (silicon adj oxide) or SiO or SiO?sub.2) with (thermal or grow or growing)) and @ay<=2001	USPAT	2004/08/10 10:45
-	270	((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)) and ((silicon adj dioxide) or (silicon adj oxide) or SiO or SiO?sub.2) with (thermal or grow or growing)) and @ay<=2001) and (etch or etching)	USPAT	2004/08/10 10:48
-	203	((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and ((polish or polishing or polished or planarize\$1 or planarizing or cmp) with (crystalline or poly\$1silicon))	USPAT	2004/08/10 15:55
-	157	((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and ((polish or polishing or polished or planarize\$1 or planarizing or cmp) with (crystalline or poly\$1silicon))) not (((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)) and ((silicon adj dioxide) or (silicon adj oxide) or SiO or SiO?sub.2) with (thermal or grow or growing)) and @ay<=2001) and (etch or etching))	USPAT	2004/08/10 15:55

-	141	(((((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and ((polish or polishing or polished or planarize\$1 or planarizing or cmp) with (crystalline or poly\$1silicon))) not ((((((titanium adj silicate) or TiSi or TiSiO or ceramic) and (crystalline adj (Si or silicon) or poly\$1silicon)) and semiconductor) and (polish or polishing or polished or planarize\$1 or planarizing or cmp)) and (((silicon adj dioxide) or (silicon adj oxide) or SiO or SiO?sub.2) with (thermal or grow or growing))) and @ay<=2001) and (etch or etching))) and @ay<=2001	USPAT	2004/08/10 15:55
-	623	titanium adj silicate	USPAT	2004/08/10 16:46
-	43	(titanium adj silicate) and (polish or polishing or cmp or planarize or planarizing)	USPAT	2004/08/10 17:34
-	5	("5272744" "5978441" "6048652" "6159643" "6159824").PN.	USPAT	2004/08/10 16:49
-	44	ULE and (polish or polishing or cmp or planarize or planarizing)	USPAT	2004/08/10 17:34
-	17	(ULE and (polish or polishing or cmp or planarize or planarizing)) and (crystal or crystalline or poly\$1silicon)	USPAT	2004/08/10 17:34
-	7	("2326059" "5154744" "5506080" "5510230" "6048652" "6159643" "6178221").PN.	USPAT	2004/08/10 17:39
-	5879	(ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)	USPAT	2004/08/11 12:03
-	1315	((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)	USPAT	2004/08/11 12:04
-	1227	((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)) and @ay<=2001	USPAT	2004/08/11 10:44
-	646	((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)) and @ay<=2001) and (lithography or lithographic or photo\$1lithograph\$2)	USPAT	2004/08/11 10:44
-	501	(((((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)) and @ay<=2001) and (lithography or lithographic or photo\$1lithograph\$2)) and ((silicon adj oxide) or (silicon adj dioxide) or siO or SiO?sub.2)	USPAT	2004/08/11 12:03
-	187	(((((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)) and @ay<=2001) and (lithography or lithographic or photo\$1lithograph\$2)) and (((silicon adj oxide) or (silicon adj dioxide) or siO or SiO?sub.2) with (thermal or anneal or annealling))	USPAT	2004/08/11 11:34

-	19	("4846931" "4883561" "5073230" "5122852" "5201996" "5286335" "5344517" "5391257" "5641381" "5764820" "5985742" "6010579" "6120597" "6159323" "6159824" "6159825" "6162705" "6204151" "6303468").PN.	USPAT	2004/08/11 11:11
-	7	("2326059" "5154744" "5506080" "5510230" "6048652" "6159643" "6178221").PN.	USPAT	2004/08/11 11:12
-	314	(((((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)) and @ay<=2001) and (lithography or lithographic or photo\$1lithograph\$2)) and ((silicon adj oxide) or (silicon adj dioxide) or siO or SiO?sub.2)) not (((((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)) and @ay<=2001) and (lithography or lithographic or photo\$1lithograph\$2)) and ((silicon adj oxide) or (silicon adj dioxide) or siO or SiO?sub.2) with (thermal or anneal or annealling)))	USPAT	2004/08/11 11:34
-	114	(((((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)) and @ay<=2001) and (lithography or lithographic or photo\$1lithograph\$2)) and ((silicon adj oxide) or (silicon adj dioxide) or siO or SiO?sub.2)) not (((((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)) and @ay<=2001) and (lithography or lithographic or photo\$1lithograph\$2)) and ((silicon adj oxide) or (silicon adj dioxide) or siO or SiO?sub.2) with (thermal or anneal or annealling))) and (molybdenum or Mo)	USPAT	2004/08/11 11:34
-	2725	(ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)	US-PGPUB; EPO; JPO	2004/08/11 12:03
-	1107	((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and @ay<=2001	US-PGPUB; EPO; JPO	2004/08/11 12:03
-	484	((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and @ay<=2001) and ((silicon adj oxide) or (silicon adj dioxide) or siO or SiO?sub.2)	US-PGPUB; EPO; JPO	2004/08/11 12:04
-	164	(((((ULE or (thermal adj expansion) or CTE! or zerodur) and (polish or polishing or cmp or planarize or planarizing)) and @ay<=2001) and ((silicon adj oxide) or (silicon adj dioxide) or siO or SiO?sub.2)) and (((crystalline or crystal) near3 (silicon or si)) or polysilicon)	US-PGPUB; EPO; JPO	2004/08/11 14:05

-	5	((("5272744") or ("5978441") or ("6048652") or ("6159643") or ("6159824")).PN.	USPAT	2004/08/11 15:00
-	1	("6613862").PN.	USPAT	2004/08/11 15:00
-	1	("6613682").PN.	USPAT	2004/08/11 15:34
-	12	("4713141" "4948462" "5372673" "5436205" "5492597" "5565681" "5605601" "5668038" "5753533" "5759920" "5779926" "5866483").PN.	USPAT	2004/08/11 15:01
-	711	mask near blank	USPAT	2004/08/11 15:34
-	11	(mask near blank) and ULE	USPAT	2004/08/11 15:36
-	117	(mask near blank) and (polish or polishing or cmp or planarize or planarization or planarizing)	USPAT	2004/08/11 15:46
-	112	((mask near blank) and (polish or polishing or cmp or planarize or planarization or planarizing)) not ((mask near blank) and ULE)	USPAT	2004/08/11 15:37
-	102	((mask near blank) and (polish or polishing or cmp or planarize or planarization or planarizing)) not ((mask near blank) and ULE)) and @ay<=2001	USPAT	2004/08/11 15:37
-	23	mask and (polish or polishing or cmp or planarize or planarization or planarizing) and (ULE or (ultra adj low adj expansion))	USPAT	2004/08/11 16:16
-	5	("5272744" "5978441" "6048652" "6159643" "6159824").PN.	USPAT	2004/08/11 15:50
-	11	ULE with (polish or polishing or cmp or polished or planarize or planarizing)	USPAT	2004/08/11 16:19
-	6	(ULE same (polish or polishing or cmp or polished or planarize or planarizing)) not (ULE with (polish or polishing or cmp or polished or planarize or planarizing))	USPAT	2004/08/11 16:19
-	17	ULE same (polish or polishing or cmp or polished or planarize or planarizing)	USPAT	2004/08/11 16:20